

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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# SOT89 NPN SILICON POWER (SWITCHING) TRANSISTOR

**FCX617** 

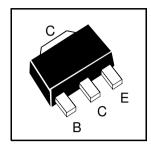
**ISSSUE 1 - NOVEMBER 1998** 

#### **FEATURES**

- \* 2W POWER DISSIPATION
- \* 12A Peak Pulse Current
- Excellent H<sub>FF</sub> Characteristics up to 12 Amps
- \* Extremely Low Saturation Voltage E.g. 8mv Typ.
  - Extremely Low Equivalent On-resistance;

 $R_{\text{CE(sat)}}$  50m $\Omega$  at 3A

Partmarking Detail - 617



#### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	15	V
Collector-Emitter Voltage	V <sub>CEO</sub>	15	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Peak Pulse Current **	I <sub>CM</sub>	12	Α
Continuous Collector Current	I <sub>C</sub>	3	Α
Base Current	I <sub>B</sub>	500	mA
Power Dissipation at T <sub>amb</sub> =25°C	P <sub>tot</sub>	1 † 2 ‡	W W
Operating and Storage Temperature Range	T <sub>j</sub> :T <sub>stg</sub>	-55 to +150	°C

<sup>†</sup> recommended Ptot calculated using FR4 measuring 15x15x0.6mm

Spice parameter data is available upon request for these devices

Refer to the handling instructions for soldering surface mount components.

<sup>\*</sup> Maximum power dissipation is calculated assuming that the device is mounted on FR4 substrate measuring 40x40x0.6mm and using comparable measurement methods adopted by other suppliers.

<sup>\*\*</sup>Measured under pulsed conditions. Pulse width=300µs. Duty cycle ≤ 2%

## **FCX617**

### ELECTRICAL CHARACTERISTICS (at T<sub>amb</sub> = 25°C unless otherwise stated).

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PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.	
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	15			٧	I <sub>C</sub> =100μA	
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	15			V	I <sub>C</sub> =10mA*	
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	5			V	I <sub>E</sub> =100μA	
Collector Cut-Off Current	I <sub>CBO</sub>		0.3	100	nA	V <sub>CB</sub> =10V	
Emitter Cut-Off Current	I <sub>EBO</sub>		0.3	100	nA	V <sub>EB</sub> =4V	
Collector Emitter Cut-Off Current	I <sub>CES</sub>		0.3	100	nA	V <sub>CES</sub> =10V	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>		8 70 150	14 100 230 300 400	mV mV mV mV	I <sub>C</sub> =0.1A, I <sub>B</sub> =10mA* I <sub>C</sub> =1A, I <sub>B</sub> =10mA* I <sub>C</sub> =3A, I <sub>B</sub> =50mA* I <sub>C</sub> =4A, I <sub>B</sub> =50mA* I <sub>C</sub> =5A, I <sub>B</sub> =50mA*	
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>		0.89	1.0	V	I <sub>C</sub> =3A, I <sub>B</sub> =50mA*	
Base-Emitter Turn-On Voltage	V <sub>BE(on)</sub>		0.82	1.0	٧	I <sub>C</sub> =3A, V <sub>CE</sub> =2V*	
Static Forward Current Transfer Ratio	h <sub>FE</sub>	200 300 200 150	415 450 320 240 80			I <sub>C</sub> =10mA, V <sub>CE</sub> =2V* I <sub>C</sub> =200mA, V <sub>CE</sub> =2V* I <sub>C</sub> =3A, V <sub>CE</sub> =2V* I <sub>C</sub> =5A, V <sub>CE</sub> =2V* I <sub>C</sub> =12A, V <sub>CE</sub> =2V*	
Transition Frequency	f <sub>T</sub>	80	120		MHz	I <sub>C</sub> =50mA, V <sub>CE</sub> =10V f=50MHz	
Output Capacitance	C <sub>obo</sub>		30	40	pF	V <sub>CB</sub> =10V, f=1MHz	
Turn-On Time	t <sub>(on)</sub>		120		ns	V <sub>CC</sub> =10V, I <sub>C</sub> =3A I <sub>B1</sub> =I <sub>B2</sub> =50mA	
Turn-Off Time	t <sub>(off)</sub>		160		ns		

<sup>\*</sup>Measured under pulsed conditions. Pulse width=300 $\mu$ s. Duty cycle  $\leq 2\%$ 

#### TYPICAL CHARACTERISTICS

